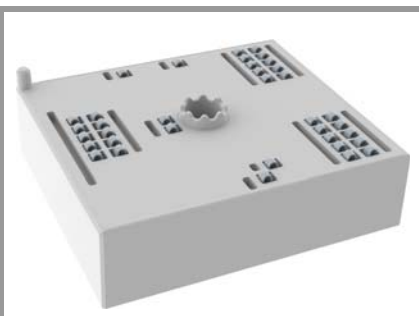


# SKiiP26GAL12T4V1



MiniSKiiP® 2

## Boost Chopper

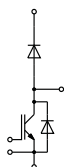
### SKiiP26GAL12T4V1

#### Features\*

- Trench 4 IGBTs
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532
- NTC T-Sensor

#### Remarks

- Max. case temperature limited to  $T_C=125^\circ\text{C}$
- Product reliability results valid for  $T_J \leq 150^\circ\text{C}$  (recommended  $T_{j,op} = -40 \dots +150^\circ\text{C}$ )
- MiniSKiiP "Technical Explanations" and "Mounting Instructions" are part of the data sheet. Please refer to both documents for further information
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- Diode 2 = D2
- IGBT 1 = T2



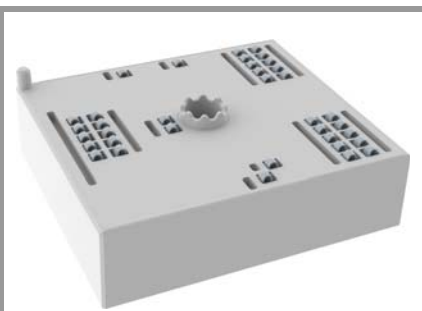
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Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT 1				
V <sub>CES</sub>	T <sub>J</sub> = 25 °C		1200	V
I <sub>C</sub>	λ <sub>paste</sub> =0.8 W/(mK) T <sub>J</sub> = 175 °C	T <sub>s</sub> = 25 °C	209	A
		T <sub>s</sub> = 70 °C	169	A
I <sub>C</sub>	λ <sub>paste</sub> =2.5 W/(mK) T <sub>J</sub> = 175 °C	T <sub>s</sub> = 25 °C	289	A
		T <sub>s</sub> = 70 °C	236	A
I <sub>Cnom</sub>			200	A
I <sub>CRM</sub>			600	A
V <sub>GES</sub>			-20 ... 20	V
t <sub>psc</sub>	V <sub>CC</sub> = 800 V V <sub>GE</sub> ≤ 15 V V <sub>CES</sub> ≤ 1200 V	T <sub>j</sub> = 150 °C	10	μs
T <sub>j</sub>			-40 ... 175	°C

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
Diode 1				
V <sub>RRM</sub>	T <sub>j</sub> = 25 °C		1200	V
I <sub>F</sub>	λ <sub>paste</sub> =0.8 W/(mK)	T <sub>s</sub> = 25 °C	174	A
		T <sub>j</sub> = 175 °C	138	A
I <sub>F</sub>	λ <sub>paste</sub> =2.5 W/(mK)	T <sub>s</sub> = 25 °C	219	A
		T <sub>j</sub> = 175 °C	174	A
I <sub>FRM</sub>			400	A
I <sub>FSM</sub>	10 ms	T <sub>j</sub> = 25 °C	990	A
	sin 180°	T <sub>j</sub> = 150 °C	990	A
T <sub>j</sub>			-40 ... 175	°C

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
Diode 2				
V <sub>RRM</sub>	T <sub>j</sub> = 25 °C		1200	V
I <sub>F</sub>	λ <sub>paste</sub> =0.8 W/(mK)	T <sub>s</sub> = 25 °C	14	A
		T <sub>j</sub> = 175 °C	12	A
I <sub>F</sub>	λ <sub>paste</sub> =2.5 W/(mK)	T <sub>s</sub> = 25 °C	15	A
		T <sub>j</sub> = 175 °C	12	A
I <sub>FRM</sub>			16	A
I <sub>FSM</sub>	10 ms	T <sub>j</sub> = 25 °C	36	A
	sin 180°	T <sub>j</sub> = 150 °C	36	A
T <sub>j</sub>			-40 ... 175	°C

Absolute Maximum Ratings			
Symbol	Conditions	Values	Unit
Module			
I <sub>t(RMS)</sub>	20 A per spring	200	A
T <sub>stg</sub>	module without TIM	-40 ... 125	°C
V <sub>isol</sub>	AC sinus 50 Hz, t = 1 min	2500	V



MiniSKiiP® 2

## Boost Chopper

### SKiiP26GAL12T4V1

#### Features\*

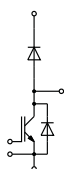
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- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532
- NTC T-Sensor

#### Remarks

- Max. case temperature limited to  $T_C=125^\circ\text{C}$
- Product reliability results valid for  $T_j \leq 150^\circ\text{C}$  (recommended  $T_{j,op} = -40 \dots +150^\circ\text{C}$ )
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- IGBT 1 = T2

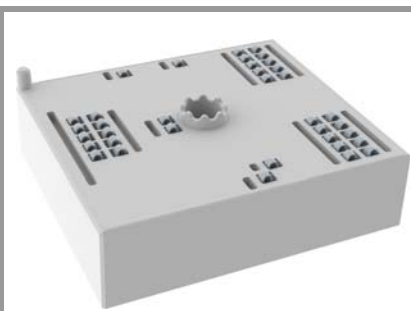
Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT 1						
V <sub>CE(sat)</sub>	I <sub>C</sub> = 200 A	T <sub>j</sub> = 25 °C		1.80	2.05	V
	V <sub>GE</sub> = 15 V chiplevel	T <sub>j</sub> = 150 °C		2.20	2.40	V
V <sub>CE0</sub>	chiplevel	T <sub>j</sub> = 25 °C		0.80	0.90	V
		T <sub>j</sub> = 150 °C		0.70	0.80	V
r <sub>CE</sub>	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25 °C		5.0	5.8	mΩ
	chiplevel	T <sub>j</sub> = 150 °C		7.5	8.0	mΩ
V <sub>GE(th)</sub>	V <sub>GE</sub> = V <sub>CE</sub> , I <sub>C</sub> = 12 mA		5	5.8	6.5	V
I <sub>CES</sub>	V <sub>GE</sub> = 0 V, V <sub>CE</sub> = 1200 V, T <sub>j</sub> = 25 °C				2.0	mA
C <sub>ies</sub>	V <sub>CE</sub> = 25 V V <sub>GE</sub> = 0 V	f = 1 MHz		12.30		nF
C <sub>oes</sub>		f = 1 MHz		0.81		nF
C <sub>res</sub>		f = 1 MHz		0.69		nF
Q <sub>G</sub>	V <sub>GE</sub> = - 8 V...+ 15 V			1130		nC
R <sub>Gint</sub>	T <sub>j</sub> = 25 °C			3.8		Ω
t <sub>d(on)</sub>	V <sub>CC</sub> = 600 V	T <sub>j</sub> = 150 °C		170		ns
t <sub>r</sub>	I <sub>C</sub> = 200 A	T <sub>j</sub> = 150 °C		45		ns
E <sub>on</sub>	V <sub>GE</sub> = +15/-15 V	T <sub>j</sub> = 150 °C		13.6		mJ
	R <sub>G on</sub> = 2 Ω	T <sub>j</sub> = 150 °C				
t <sub>d(off)</sub>	R <sub>G off</sub> = 2 Ω	T <sub>j</sub> = 150 °C		440		ns
t <sub>f</sub>	di/dt <sub>on</sub> = 5500 A/μs	T <sub>j</sub> = 150 °C		91		ns
	di/dt <sub>off</sub> = 2000 A/μs	T <sub>j</sub> = 150 °C				
E <sub>off</sub>	dv/dt = 7000 V/μs					
	L <sub>s</sub> = 25 nH			22.1		mJ
R <sub>th(j-s)</sub>	per IGBT, λ <sub>paste</sub> =0.8 W/(mK)			0.28		K/W
R <sub>th(j-s)</sub>	per IGBT, λ <sub>paste</sub> =2.5 W/(mK)			0.16		K/W

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Diode 1						
V <sub>F</sub>	I <sub>F</sub> = 200 A	T <sub>j</sub> = 25 °C		2.20	2.52	V
	V <sub>GE</sub> = 0 V chiplevel	T <sub>j</sub> = 150 °C		2.15	2.47	V
V <sub>F0</sub>	chiplevel	T <sub>j</sub> = 25 °C		1.30	1.50	V
		T <sub>j</sub> = 150 °C		0.90	1.10	V
r <sub>F</sub>	chiplevel	T <sub>j</sub> = 25 °C		4.5	5.1	mΩ
		T <sub>j</sub> = 150 °C		6.3	6.9	mΩ
I <sub>RRM</sub>	I <sub>F</sub> = 200 A	T <sub>j</sub> = 150 °C		228		A
Q <sub>rr</sub>	di/dt <sub>off</sub> = 5215 A/μs	T <sub>j</sub> = 150 °C		32		μC
E <sub>rr</sub>	V <sub>GE</sub> = -15 V V <sub>CC</sub> = 600 V	T <sub>j</sub> = 150 °C		13.4		mJ
R <sub>th(j-s)</sub>	per Diode, λ <sub>paste</sub> =0.8 W/(mK)			0.4		K/W
R <sub>th(j-s)</sub>	per Diode, λ <sub>paste</sub> =2.5 W/(mK)			0.28		K/W



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# SKiiP26GAL12T4V1



MiniSKiiP® 2

## Boost Chopper

### SKiiP26GAL12T4V1

#### Features\*

- Trench 4 IGBTs
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532
- NTC T-Sensor

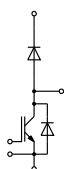
#### Remarks

- Max. case temperature limited to  $T_C=125^{\circ}\text{C}$
- Product reliability results valid for  $T_j \leq 150^{\circ}\text{C}$  (recommended  $T_{j,op} = -40 \dots +150^{\circ}\text{C}$ )
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- For storage and case temperature with TIM see document: "Technical Explanations Thermal Interface Materials"
- Diode 1 = D1
- Diode 2 = D2
- IGBT 1 = T2

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Diode 2						
V <sub>F</sub>	I <sub>F</sub> = 8 A	T <sub>j</sub> = 25 °C		2.33	2.65	V
	V <sub>GE</sub> = 0 V chiplevel	T <sub>j</sub> = 150 °C		2.35	2.68	V
V <sub>F0</sub>	chiplevel	T <sub>j</sub> = 25 °C		1.30	1.50	V
		T <sub>j</sub> = 150 °C		0.90	1.10	V
r <sub>F</sub>	chiplevel	T <sub>j</sub> = 25 °C		129	144	mΩ
		T <sub>j</sub> = 150 °C		181	198	mΩ
I <sub>RRM</sub>	I <sub>F</sub> = 8 A	T <sub>j</sub> = 150 °C		t.b.d.		A
Q <sub>rr</sub>	V <sub>GE</sub> = -15 V V <sub>CC</sub> = 600 V	T <sub>j</sub> = 150 °C		t.b.d.		μC
E <sub>rr</sub>		T <sub>j</sub> = 150 °C		t.b.d.		mJ
R <sub>th(j-s)</sub>	per Diode, λ <sub>paste</sub> =0.8 W/(mK)			2.8		K/W
R <sub>th(j-s)</sub>	per Diode, λ <sub>paste</sub> =2.5 W/(mK)			2.6		K/W

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
Module					
M <sub>s</sub>	to heat sink	2		2.5	Nm
w	weight		55		g

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
Temperature Sensor					
R <sub>100</sub>	T <sub>c</sub> =100°C (R <sub>25</sub> =5 kΩ)		493 ± 5%		Ω
B <sub>25/85</sub>	R <sub>(T)</sub> =R <sub>25</sub> *exp[B <sub>25/85</sub> *(1/T-1/298)], T[K]		3420		K



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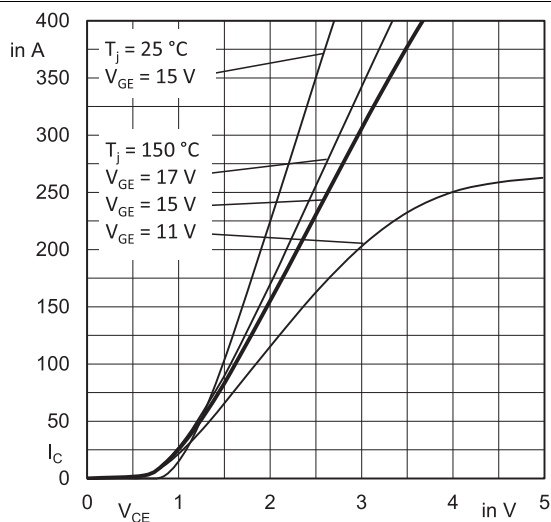


Fig. 1: Typ. output characteristic, inclusive  $R_{CC'} + E_{E'}$

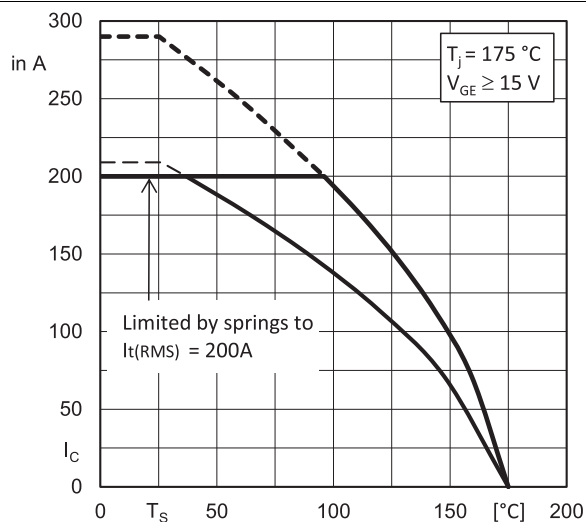


Fig. 2: Rated current vs. temperature  $I_C = f(T_s)$

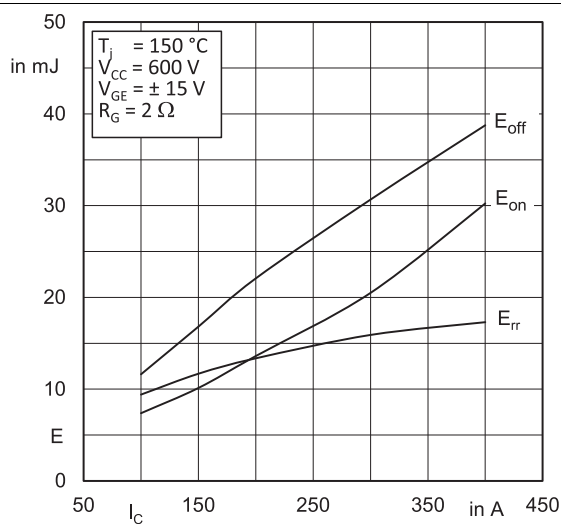


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

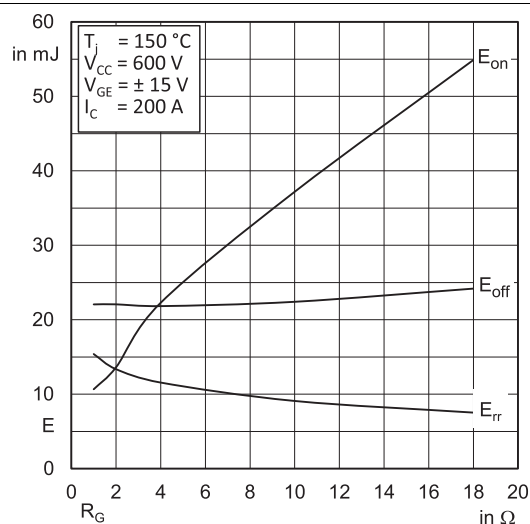


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

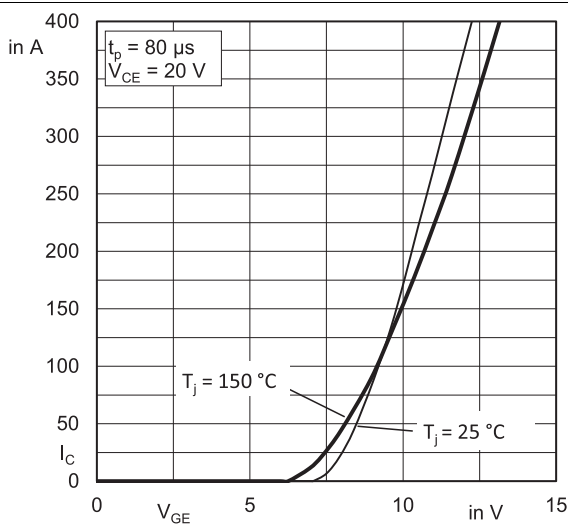


Fig. 5: Typ. transfer characteristic

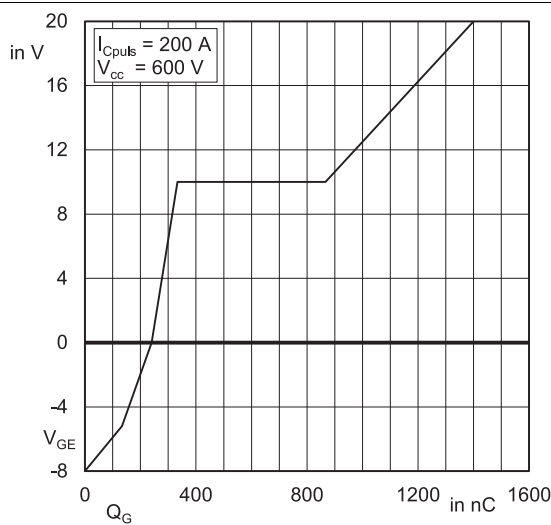


Fig. 6: Typ. gate charge characteristic

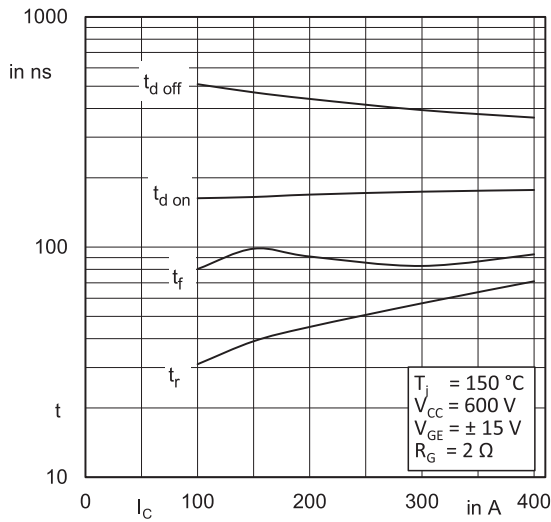


Fig. 7: Typ. switching times vs.  $I_C$

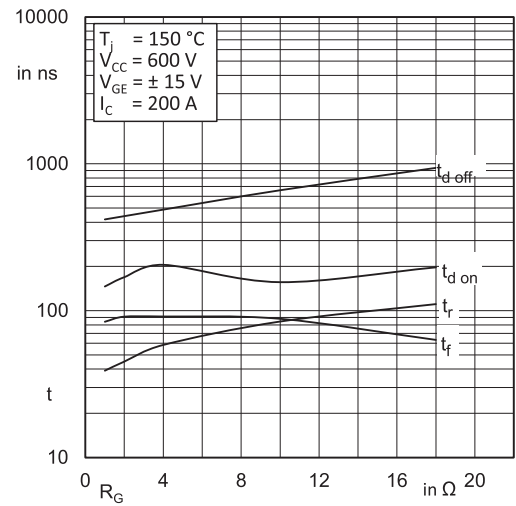


Fig. 8: Typ. switching times vs. gate resistor  $R_G$

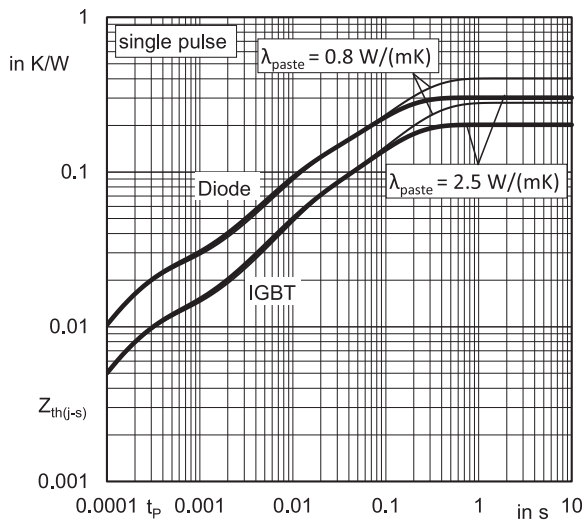


Fig. 9: Typ. transient thermal impedance

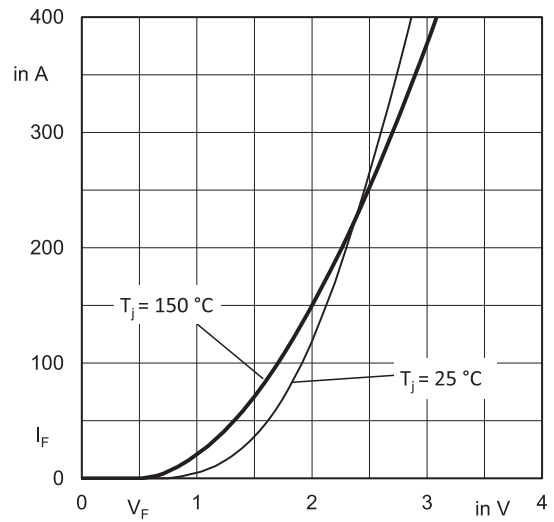


Fig. 10: Typ. CAL diode forward charact., incl.  $R_{CC}'+EE'$

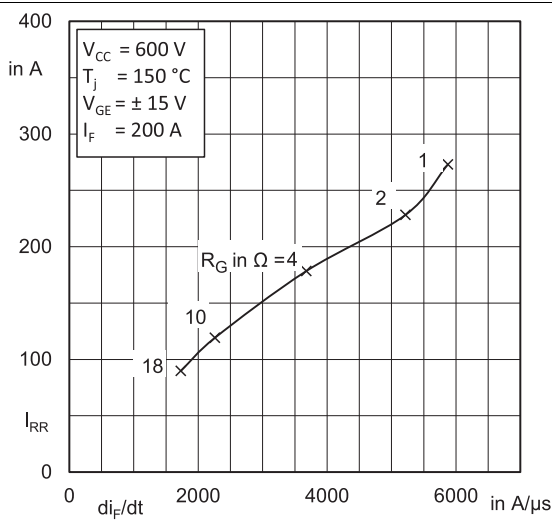


Fig. 11: Typ. CAL diode peak reverse recovery current

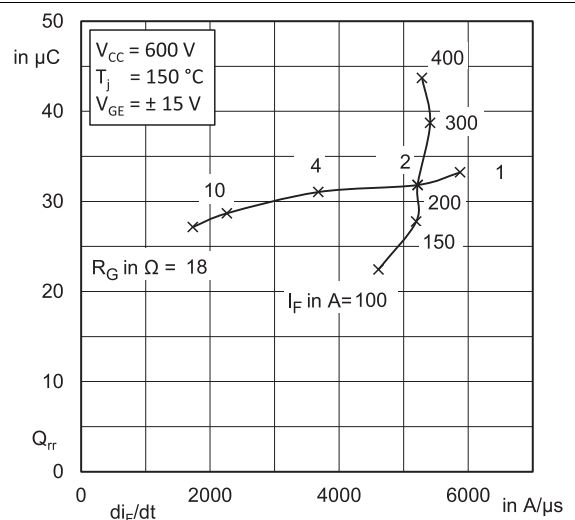
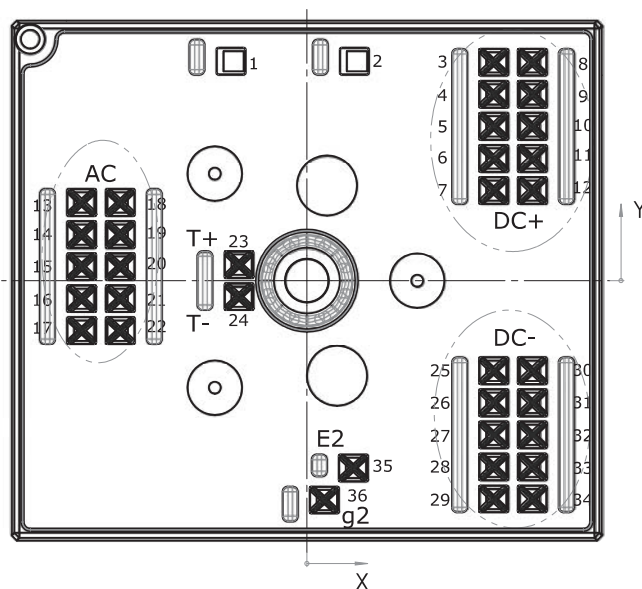


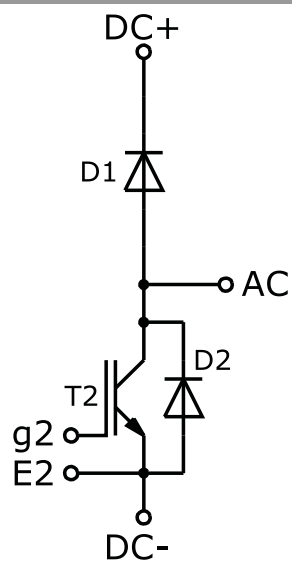
Fig. 12: Typ. CAL diode recovery charge

Pin out							
Pin	X	Y	Function	Pin	X	Y	Function
1	-7,58	21,9		19	-18,63	4,6	AC
2	4,73	21,9		20	-18,63	1,4	AC
3	18,63	21,8	DC+	21	-18,63	-1,8	AC
4	18,63	18,6	DC+	22	-18,63	-5	AC
5	18,63	15,4	DC+	23	-6,78	1,6	T+
6	18,63	12,2	DC+	24	-6,78	-1,6	T-
7	18,63	9	DC+	25	18,63	-9	DC-
8	22,48	21,8	DC+	26	18,63	-12,2	DC-
9	22,48	18,6	DC+	27	18,63	-15,4	DC-
10	22,48	15,4	DC+	28	18,63	-18,6	DC-
11	22,48	12,2	DC+	29	18,63	-21,8	DC-
12	22,48	9	DC+	30	22,48	-9	DC-
13	-22,48	7,8	AC	31	22,48	-12,2	DC-
14	-22,48	4,6	AC	32	22,48	-15,4	DC-
15	-22,48	1,4	AC	33	22,48	-18,6	DC-
16	-22,48	-1,8	AC	34	22,48	-21,8	DC-
17	-22,48	-5	AC	35	4,63	-18,7	E2
18	-18,63	7,8	AC	36	1,73	-21,9	q2

all values in mm



Pinout and Dimensions



Pinout

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

## **\*IMPORTANT INFORMATION AND WARNINGS**

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